

ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18

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Title of Invention

**METHOD OF FORMING FET SILICIDE GATE STRUCTURES
INCORPORATING INNER SPACERS**

Application Number :

Confirmation Number:

First Named Applicant: Victor Ku

Attorney Docket Number: FIS920030341

Art Unit:

Examiner:

Search string: (6376888 or 6373111 or 5619057 or 6501131 or 6355531 or 4745079 or 20030119292 or 20020179975 or 20020086504 or 20020123189 or 20030011037 or 20030075766).pn

US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
PD	1	6376888	2002-04-23	Tsunashima et al.	—	—	—
↑	2	6373111	2002-04-16	Zheng et al.	—	—	—
↑	3	5619057	1997-04-08	Komatsu	—	—	—
↑	4	6501131	2002-12-31	Divakaruni et al.	—	—	—
✓	5	6355531	2002-03-12	Mandelman et al.	—	—	—
PD	6	4745079	1988-05-17	Pfister	—	—	—

US Published Applications

Note: Applicant is not required to submit a paper copy of cited US Published Applications

init	Cite.No.	Pub. No.	Date	Applicant	Kind	Class	Subclass
PD	1	20030119292	2003-06-26	Lee et al.	—	—	—
↑	2	20020179975	2002-12-05	Wakabayashi et al.	—	—	—
↑	3	20020086504	2002-07-04	Park et al.	—	—	—
↑	4	20020123189	2002-09-05	Cha et al.	—	—	—
✓	5	20030011037	2003-01-16	Chau et al.	—	—	—
PD	6	20030075766	2003-04-24	Lin et al.	—	—	—

Signature

Examiner Name	Date
PHUC T. DANG	4/20/2005